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SEMICONDUCTOR

November 2013

FQB44N10 N-Channel QFET® MOSFET

100 V, 43.5 A, 39 m Ω

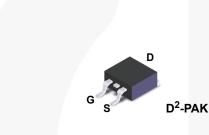
Description

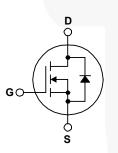
This N-Channel enhancement mode power MOSFET is • 43.5 A, 100 V, $R_{DS(on)}$ = 39 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state $I_D = 21.75 \text{ A}$ Low Gate Charge (Typ. 48 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 85 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- I_D = 21.75 A

- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	Parameter		FQB44N10TM	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		43.5	A
	- Continuous (T _C = 100°C)		30.8	A
I _{DM}	Drain Current - Pulsed	- Pulsed (Note 1)		
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	530	mJ
I _{AR}	Avalanche Current	(Note 1)	43.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	14.6	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
PD	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.75	W
	Power Dissipation ($T_C = 25^{\circ}C$)		146	W
	- Derate above 25°C		0.97	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C

Thermal Characteristics

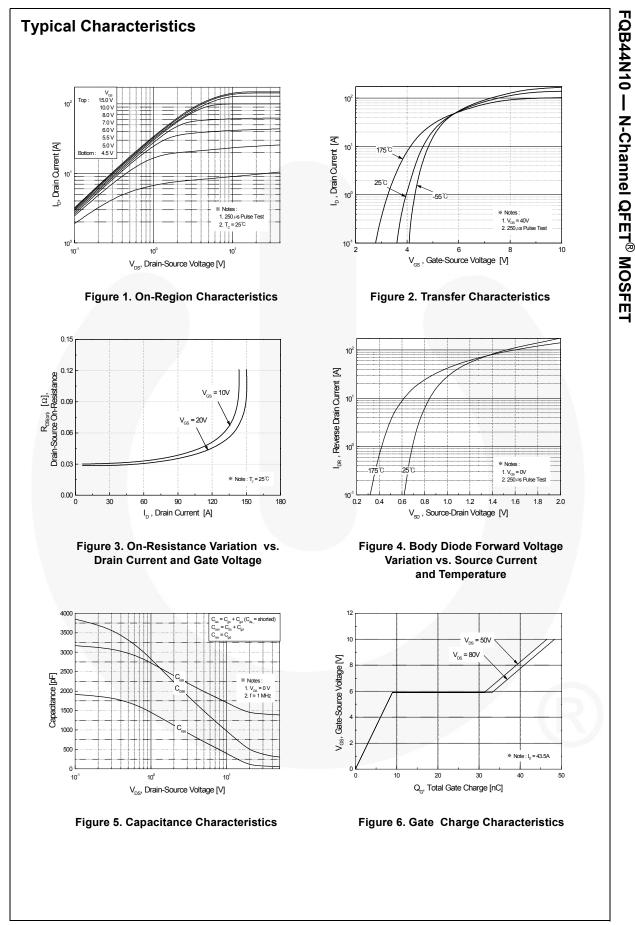
Symbol	Parameter	FQB44N10TM	Unit
R_{\thetaJC}	Thermal Resistance, Junction to Case, Max.	1.03	
P	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

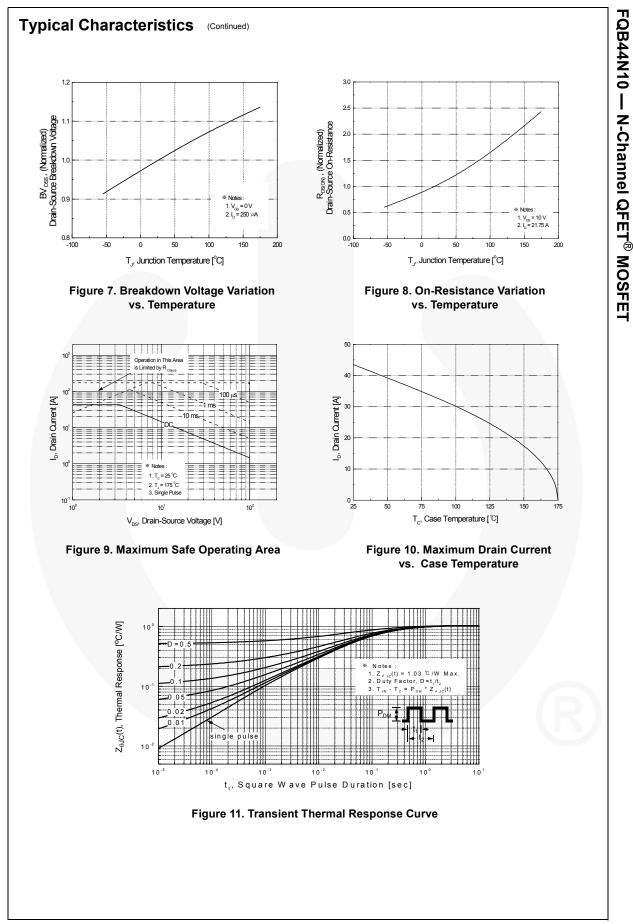
Faiti	•		Pack	kage Packing Method R		Reel	Size	Tape Width		Quantity	
FQB44			PAK Tape and Reel 330			mm	24 mm		800 units		
Electri	cal Chai	racteristics	T _C = 25°0	C unless oth	nerwise noted.						
Symbol		Parameter			Test Con	ditions		Min.	Тур.	Max.	Unit
Off Cha	aracteristi	ice									
BV _{DSS}	Drain-Source Breakdown Voltage		Vcs =	$0 V l_{\rm D} = 2!$	100			V			
ΔBV _{DSS}	5		$V_{GS} = 0 V, I_D = 250 \mu A$			100					
$/\Delta T_{J}$	Coefficient	Breakdown Voltage Temperature Coefficient		I_D = 250 µA, Referenced to 25°C					0.1		V/°C
IDSS			_	V _{DS} = 100 V, V _{GS} = 0 V					1	μA	
000	Zero Gate	Voltage Drain Curr	ent	$V_{DS} = 80 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{C}$						10	μΑ
I _{GSSF}	Gate-Body	Gate-Body Leakage Current, Forward		-	25 V, V _{DS} -			100	nA		
I _{GSSR}	,	Leakage Current,			-25 V, V _{DS}					-100	nA
									1		
	racteristi	cs									
V _{GS(th)}	Gate Three	shold Voltage	_	$V_{DS} = 1$	V _{GS} , I _D = 2	250 μA		2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} = 10 V, I _D = 21.75 A				0.03	0.039	Ω		
9 _{FS}	Forward T	ransconductance		V _{DS} =	40 V, I _D = 2	21.75 A			30		S
Dynam	ic Charac	toristics									
bynann		ici istics									
C _{iss}	Input Capa		-	V _{DS} =	25 V, V _{GS} :	= 0 V,			1400	1800	pF
C _{iss}	1	acitance	-	V _{DS} = f = 1.0	25 V, V _{GS} : MHz	= 0 V,			1400 425	1800 550	pF pF
	Input Capa Output Ca	acitance	e			= 0 V,					
C _{iss} C _{oss} C _{rss}	Input Capa Output Ca Reverse T	acitance pacitance ransfer Capacitanc	e			= 0 V,			425	550	pF
C _{iss} C _{oss} C _{rss} Switchi	Input Capa Output Ca Reverse Ti ing Chara	acitance pacitance ransfer Capacitanc I cteristics	e			= 0 V,			425 85	550 110	pF
C _{iss} C _{oss} C _{rss} Switchi	Input Capa Output Ca Reverse Ti ing Chara Turn-On D	acitance pacitance ransfer Capacitanc Icteristics lelay Time	e	f = 1.0					425 85 19	550 110 45	pF pF ns
$\frac{C_{iss}}{C_{oss}}$ $\frac{C_{rss}}{C_{rss}}$ Switchi $t_{d(on)}$ t_r	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R	acitance pacitance ransfer Capacitanc acteristics elay Time ise Time	e	f = 1.0	MHz 50 V, I _D = 4				425 85 19 190	550 110 45 390	pF pF ns ns
C_{iss} C_{oss} C_{rss} Switchi $t_{d(on)}$ t_r $t_{d(off)}$	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D	acitance pacitance ransfer Capacitanc Icteristics elay Time ise Time elay Time	e	f = 1.0	MHz 50 V, I _D = 4	43.5 A,	(Note 4)	 	425 85 19 190 90	550 110 45 390 190	pF pF ns ns ns
$\frac{C_{iss}}{C_{oss}}$ C_{rss} Switchi $t_{d(on)}$ t_{r} $t_{d(off)}$ t_{f}	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F	acitance pacitance ransfer Capacitanc Icteristics elay Time elay Time elay Time all Time	e	f = 1.0	MHz 50 V, I _D = 4 5 Ω	43.5 A,	(Note 4)	 	425 85 19 190 90 100	550 110 45 390 190 210	pF pF ns ns ns ns
$\begin{array}{c} \hline C_{iss} \\ \hline C_{oss} \\ \hline C_{rss} \\ \hline \\ $	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge	e	f = 1.0 V _{DD} = R _G = 2 V _{DS} =	MHz 50 V, I _D = 4 5 Ω 80 V, I _D = 4	43.5 A,	(Note 4)	 	425 85 19 190 90 100 48	550 110 45 390 190 210 62	pF pF ns ns ns ns nc
$\begin{array}{c} \hline C_{iss} \\ \hline C_{oss} \\ \hline C_{rss} \\ \hline \\ $	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sour	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge	e	f = 1.0	MHz 50 V, I _D = 4 5 Ω 80 V, I _D = 4	13.5 A, 13.5 A,		 	425 85 19 190 90 100 48 9.0	550 110 45 390 190 210 62 	pF pF ns ns ns ns nC nC
$\begin{array}{c} \hline C_{iss} \\ \hline C_{oss} \\ \hline C_{rss} \\ \hline \\ $	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge	e	f = 1.0 V _{DD} = R _G = 2 V _{DS} =	MHz 50 V, I _D = 4 5 Ω 80 V, I _D = 4	13.5 A, 13.5 A,	(Note 4) (Note 4)	 	425 85 19 190 90 100 48	550 110 45 390 190 210 62	pF pF ns ns ns ns nc
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sour Gate-Drair	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge n Charge		$f = 1.0$ $V_{DD} =$ $R_{G} = 2$ $V_{DS} =$ $V_{GS} =$	MHz 50 V, I _D = 4 5 Ω 80 V, I _D = 4 10 V	43.5 A, 13.5 A,		 	425 85 19 190 90 100 48 9.0	550 110 45 390 190 210 62 	pF pF ns ns ns ns nC nC
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \\ \end{array} \\ \begin{array}{c} \textbf{Switchi} \\ t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \\ Q_{g} \\ Q_{gs} \\ Q_{gd} \\ \end{array} \\ \begin{array}{c} \textbf{Drain-S} \end{array}$	Input Capa Output Ca Reverse T ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sour Gate-Drair	acitance pacitance ransfer Capacitance acteristics elay Time elay Time all Time Charge ce Charge the Charge ode Character	stics ar	$f = 1.0$ $V_{DD} =$ $R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $N_{GS} = 2$	MHz 50 V, I _D = 4 5 Ω 80 V, I _D = 4 10 V	43.5 A, 43.5 A, 43.5 A,		 	425 85 19 190 90 100 48 9.0 24	550 110 45 390 190 210 62 	pF pF ns ns ns nC nC nC
$\begin{array}{c} \hline C_{iss} \\ \hline C_{oss} \\ \hline C_{rss} \\ \hline \\ $	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sour Gate-Drair Cource Dia Maximum	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge ce Charge ode Character Continuous Drain-5	istics ar	$f = 1.0$ $V_{DD} =$ $R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ Max Max $Max = 0$ $Max = 0$	MHz $50 \text{ V}, \text{ I}_{\text{D}} = 4$ 5Ω $80 \text{ V}, \text{ I}_{\text{D}} = 4$ 10 V kimum R rard Curren	43.5 A, 43.5 A, 43.5 A,		 	425 85 19 190 90 100 48 9.0 24	550 110 45 390 190 210 62 43.5	PF pF ns ns ns nC nC nC A
Ciss Coss Crss Switchi td(on) tr td(off) tr Qg Qgs Qgd Drain-S Is	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off Fa Total Gate Gate-Sour Gate-Drair Cource Did Maximum	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge ce Charge ode Character Continuous Drain-S	i stics ar Source Dic ce Diode F	$f = 1.0$ $V_{DD} =$ $R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $M_{GS} =$	MHz $50 \text{ V}, \text{ I}_{\text{D}} = 4$ 5Ω $80 \text{ V}, \text{ I}_{\text{D}} = 4$ 10 V kimum R rard Current	43.5 A, 43.5 A, 43.5 A, atings t		 	425 85 19 190 90 100 48 9.0 24 	550 110 45 390 190 210 62 43.5 174	PF pF ns ns ns nC nC nC nC A A
$\begin{array}{c} C_{iss} \\ C_{oss} \\ C_{rss} \end{array}$	Input Capa Output Ca Reverse Tr ing Chara Turn-On D Turn-Off D Turn-Off Fa Total Gate Gate-Sour Gate-Drair Source Di d Maximum Drain-Sour	acitance pacitance ransfer Capacitanc acteristics elay Time elay Time elay Time all Time Charge ce Charge ce Charge ode Character Continuous Drain-5	i stics ar Source Dic ce Diode F	$f = 1.0$ $V_{DD} =$ $R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $M Max$ $M Max$ $M Max$ $M Max$ $M M Max$	MHz $50 \text{ V}, \text{ I}_{\text{D}} = 4$ 5Ω $80 \text{ V}, \text{ I}_{\text{D}} = 4$ 10 V kimum R rard Curren	43.5 A, 43.5 A, 43.5 A, 43.5 A		 	425 85 19 190 90 100 48 9.0 24	550 110 45 390 190 210 62 43.5	PF pF ns ns ns nC nC nC A

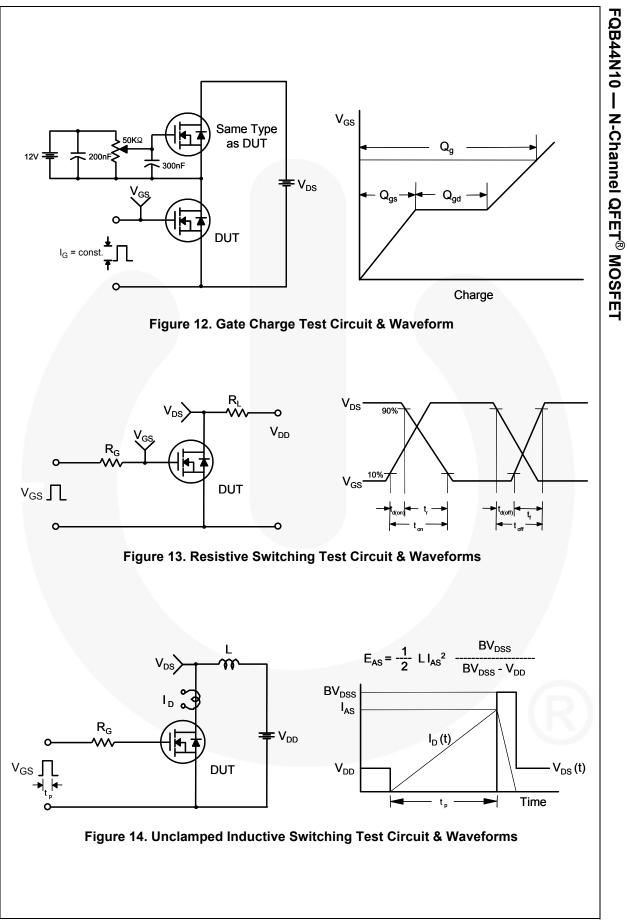
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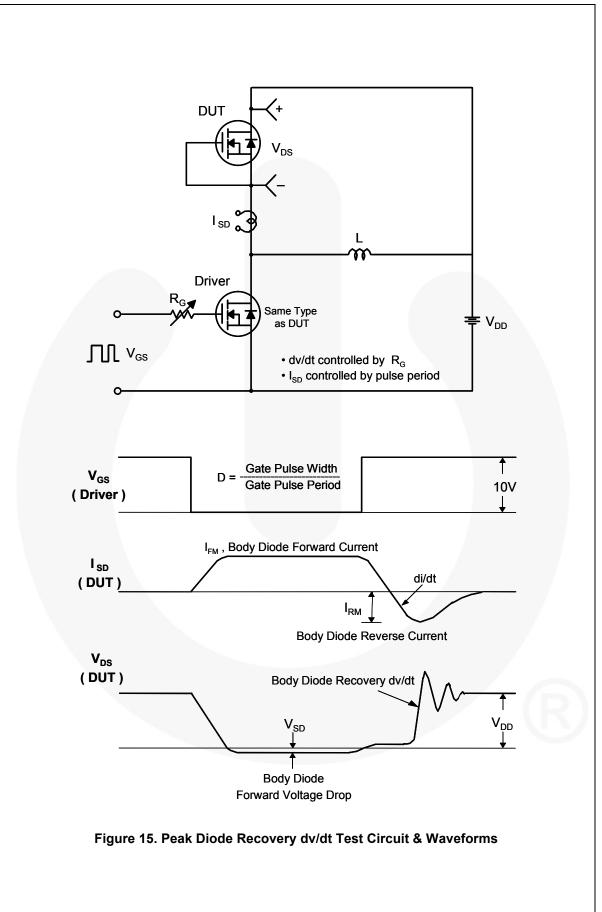
1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 0.42 mH, I_{AS} = 43.5 Å, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C. 3. $I_{SD} \le 43.5$ Å, di/dt $\le 300 \text{ A/}\mu\text{s}$, $V_{DD} \le BV_{DSS}$ starting T_J = 25°C. 4. Essentially independent of operating temperature.

FQB44N10 — N-Channel QFET[®] MOSFET









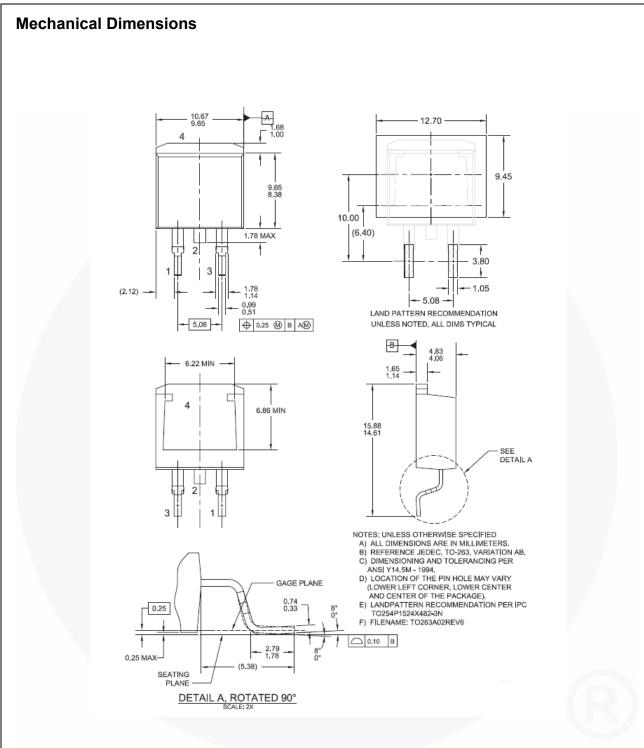


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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